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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HAT1044M

Silicon P Channel Power MOS FET
Power Switching

RENESAS

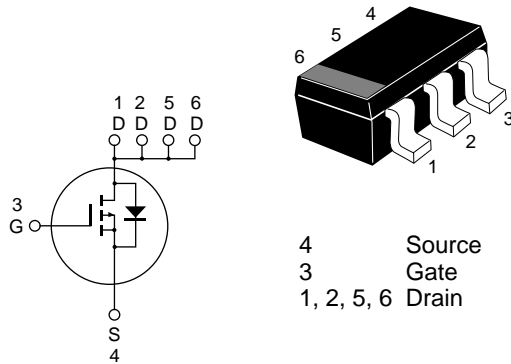
ADE-208-753D (Z)
Preliminary
5th. Edition
December 1998

Features

- Low on-resistance
- Low drive current
- High density mounting
- 4.5V gate drive device can be driven from 5V source

Outline

TSOP-6



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D^{*2}	-4.5	A
Drain peak current	$I_{D(pulse)}^{*1}$	-18	A
Body-drain diode reverse drain current	I_{DR}^{*2}	-4.5	A
Channel dissipation	$Pch_{(pulse)}^{*2}$	2.0	W
	$Pch_{(continuous)}^{*3}$	1.05	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$

2. When using the alumina ceramic board (50 x 50 x 0.7 mm), $PW \leq 5s, Ta = 25^\circ C$

3. When using the alumina ceramic board (50 x 50 x 0.7 mm), $Ta = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

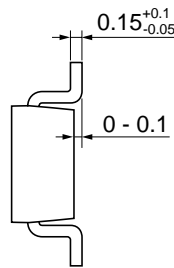
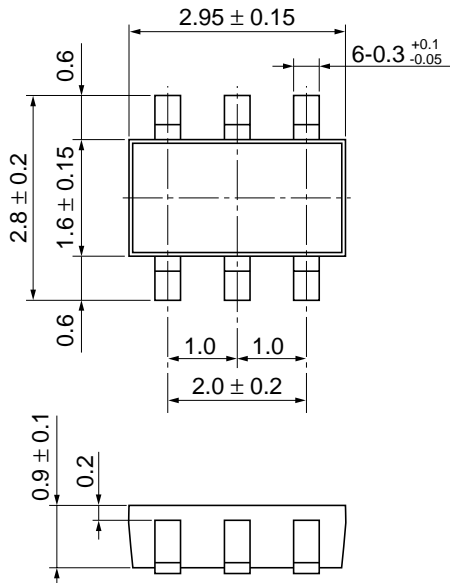
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10mA, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -30V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain to source on state resistance	$R_{DS(on)}$	—	50	60	m Ω	$I_D = -3A, V_{GS} = -10V^{*1}$
	$R_{DS(on)}$	—	80	105	m Ω	$I_D = -3A, V_{GS} = -4.5V^{*1}$
Forward transfer admittance	$ y_{fs} $	3	5.5	—	S	$I_D = -3A, V_{DS} = -10V^{*1}$
Input capacitance	Ciss	—	600	—	pF	$V_{DS} = -10V$
Output capacitance	Coss	—	220	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	150	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$V_{GS} = -10V, I_D = -3A$
Rise time	t_r	—	85	—	ns	$R_L = 3.3\Omega$
Turn-off delay time	$t_{d(off)}$	—	55	—	ns	
Fall time	t_f	—	55	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-0.95	—	V	$IF = -4.5A, V_{GS} = 0^{*1}$
Body-drain diode reverse recovery time	t_{rr}	—	50	—	ns	$IF = -4.5A, V_{GS} = 0$ $diF/dt = -20A/\mu s$

Note: 1. Pulse test

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TSOP-6
JEDEC	—
EIAJ	—
Mass (reference value)	0.012 g

Cautions

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